Bidirectional voltage level translator

- Low 3.5 Ω ON-state connection between input and output ports provides less signal distortion
- 5 V tolerant I/O ports to support mixed-mode signal operation
- High-impedance An and Bn pins for EN = LOW
- Lock-up free operation
- Flow through pinout for ease of printed-circuit board trace routing
- ESD protection exceeds 4 kV HBM per JESD22-A114 and 1000 V CDM per JESD22-C101

3. Ordering information

Table 1. Ordering information

 $T_{amb} = -40 \, ^{\circ}\text{C} \text{ to } +105 \, ^{\circ}\text{C}.$

Type number	Topside	Number	Package				
	marking	of bits	Name	Description	Version		
NVT2002DP[1]	N2002	2	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm	SOT505-1		
NVT2002GD	N02	2	XSON8U	plastic extremely thin small outline package; no leads; 8 terminals; UTLP based; body $3\times2\times0.5$ mm	SOT996-2		
NVT2001GM	N1	1	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1.45 \times 0.5 mm	SOT886		
NVT2001GM	T1	1	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1.45 \times 0.5 mm; requires SSB	SOT886		

^[1] GTL2002DP = NVT2002DP.

3.1 Ordering options

Table 2. Ordering options

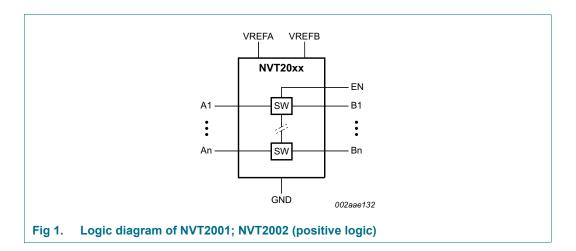
Type number	Orderable part number	Package	Packing method	Minimum order quantity	Temperature
NVT2002DP	NVT2002DP,118	TSSOP8	Reel 13" Q1/T1 *Standard mark SMD	2500	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +105 ^{\circ}\text{C}$
NVT2002GD	NVT2002GD,125	XSON8U	Reel 7" Q3/T4 *Standard mark	3000	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +105 ^{\circ}\text{C}$
NVT2001GM	NVT2001GM,115[1]	XSON6	Reel 7" Q1/T1 *Standard mark SMD	5000	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +105 ^{\circ}\text{C}$
NVT2001GM	NVT2001GMZ	XSON6	Reel 7" Q1/T1 *Standard mark SMD SSB[2]	5000	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +105 ^{\circ}\text{C}$

^[1] Will go EOL - migrate to new leadframe orderable part number NVT2001GMZ.

^[2] This packing method uses a Static Shielding Bag (SSB) solution. Material is to be kept in the sealed bag between uses.

Bidirectional voltage level translator

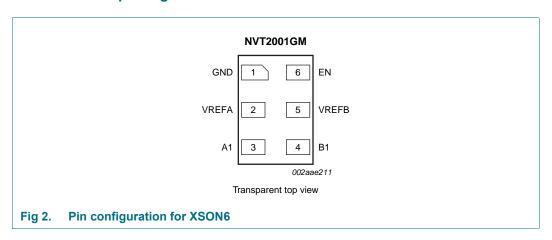
4. Functional diagram



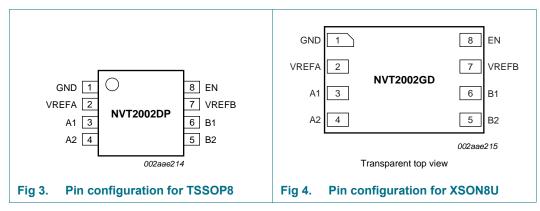
5. Pinning information

5.1 Pinning

5.1.1 1-bit in XSON6 package



5.1.2 2-bit in TSSOP8 and XSON8U packages



NVT2001_NVT2002

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5.2 Pin description

Table 3. Pin description

Symbol	Pin		Description
	NVT2001[1]	NVT2002[2]	
GND	1	1	ground (0 V)
VREFA	2	2	low-voltage side reference supply voltage for An
A1	3	3	low-voltage side; connect to VREFA through a pull-up
A2	-	4	resistor
B1	4	6	high-voltage side; connect to VREFB through a pull-up
B2	-	5	resistor
VREFB	5	7	high-voltage side reference supply voltage for Bn
EN	6	8	switch enable input; connect to VREFB and pull-up through a high resistor

^{[1] 1-}bit NVT2001 available in XSON6 package.

6. Functional description

Refer to Figure 1 "Logic diagram of NVT2001; NVT2002 (positive logic)".

6.1 Function table

Table 4. Function selection (example)

H = HIGH level; L = LOW level.

Input EN[1]	Function
Н	An = Bn
L	disconnect

^[1] EN is controlled by the V_{ref(B)} logic levels and should be at least 1 V higher than V_{ref(A)} for best translator operation.

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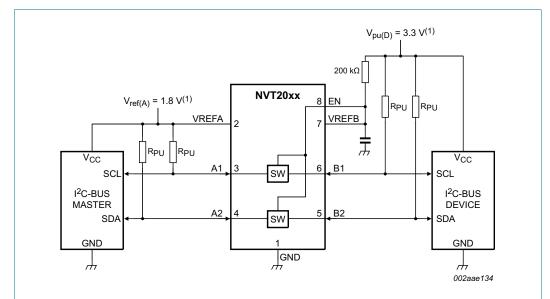
^{[2] 2-}bit NVT2002 available in TSSOP8 and XSON8U packages.

7. Application design-in information

The NVT2001/02 can be used in level translation applications for interfacing devices or systems operating at different interface voltages with one another. The NVT2001/02 is ideal for use in applications where an open-drain driver is connected to the data I/Os. The NVT2001/02 can also be used in applications where a push-pull driver is connected to the data I/Os.

7.1 Enable and disable

The NVT20xx has an EN input that is used to disable the device by setting EN LOW, which places all I/Os in the high-impedance state.



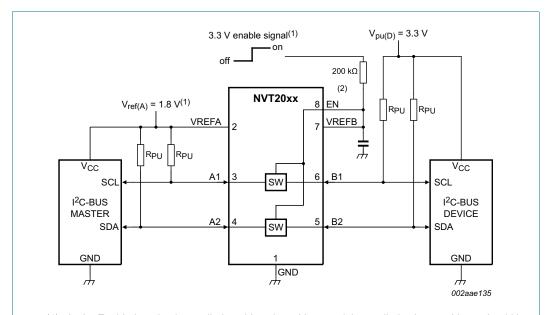
(1) The applied voltages at $V_{ref(A)}$ and $V_{pu(D)}$ should be such that $V_{ref(B)}$ is at least 1 V higher than $V_{ref(A)}$ for best translator operation.

Fig 5. Typical application circuit (switch always enabled)

Table 5. Application operating conditions *Refer to Figure 5.*

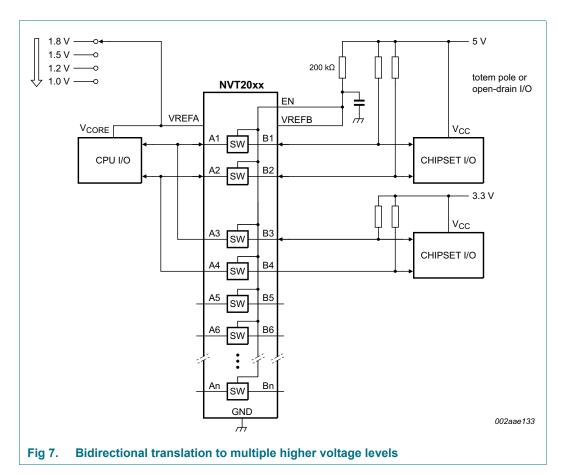
Symbol	Parameter	Conditions	Min	Typ[1]	Max	Unit
V _{ref(B)}	reference voltage (B)		$V_{ref(A)} + 0.6$	2.1	5	V
$V_{I(EN)}$	input voltage on pin EN		$V_{ref(A)} + 0.6$	2.1	5	V
$V_{ref(A)}$	reference voltage (A)		0	1.5	4.4	V
I _{sw(pass)}	pass switch current		-	14	-	mA
I _{ref}	reference current	transistor	-	5	-	μΑ
T _{amb}	ambient temperature	operating in free-air	-40	-	+105	°C

[1] All typical values are at T_{amb} = 25 °C.



- (1) In the Enabled mode, the applied enable voltage $V_{I(EN)}$ and the applied voltage at $V_{ref(A)}$ should be such that $V_{ref(B)}$ is at least 1 V higher than $V_{ref(A)}$ for best translator operation.
- (2) Note that the enable time and the disable time are essentially controlled by the RC time constant of the capacitor and the 200 k Ω resistor on the EN pin.

Fig 6. Typical application circuit (switch enable control)



Bidirectional voltage level translator

7.2 Bidirectional translation

For the bidirectional clamping configuration (higher voltage to lower voltage or lower voltage to higher voltage), the EN input must be connected to VREFB and both pins pulled to HIGH side $V_{pu(D)}$ through a pull-up resistor (typically 200 k Ω). This allows VREFB to regulate the EN input. A filter capacitor on VREFB is recommended. The master output driver can be totem pole or open-drain (pull-up resistors may be required) and the slave device output can be totem pole or open-drain (pull-up resistors are required to pull the Bn outputs to $V_{pu(D)}$). However, if either output is totem-pole, data must be unidirectional or the outputs must be 3-stateable and be controlled by some direction-control mechanism to prevent HIGH-to-LOW contentions in either direction. If both outputs are open-drain, no direction control is needed.

The reference supply voltage $(V_{ref(A)})$ is connected to the processor core power supply voltage. When VREFB is connected through a 200 k Ω resistor to a 3.3 V to 5.5 V $V_{pu(D)}$ power supply, and $V_{ref(A)}$ is set between 1.0 V and $(V_{pu(D)}-1 \text{ V})$, the output of each An has a maximum output voltage equal to VREFA, and the output of each Bn has a maximum output voltage equal to $V_{pu(D)}$.

7.3 How to size pull-up resistor value

Sizing the pull-up resistor on an open-drain bus is specific to the individual application and is dependent on the following driver characteristics:

- · The driver sink current
- The V_{OL} of driver
- The V_{IL} of the driver
- Frequency of operation

The following tables can be used to estimate the pull-up resistor value in different use cases so that the minimum resistance for the pull-up resistor can be found.

Table 6, Table 7 and Table 8 contain suggested minimum values of pull-up resistors for the PCA9306 and NVT20xx devices with typical voltage translation levels and drive currents. The calculated values assume that both drive currents are the same. $V_{OL} = V_{IL} = 0.1 \times V_{CC} \text{ and accounts for a } \pm 5 \text{ % V}_{CC} \text{ tolerance of the supplies, } \pm 1 \text{ % resistor values. It should be noted that the resistor chosen in the final application should be equal to or larger than the values shown in Table 6, Table 7 and Table 8 to ensure that the pass voltage is less than 10 % of the <math>V_{CC}$ voltage, and the external driver should be able to sink the total current from both pull-up resistors. When selecting the minimum resistor value in Table 6, Table 7 or Table 8, the drive current strength that should be chosen should be the lowest drive current seen in the application and account for any drive strength current scaling with output voltage. For the GTL devices, the resistance table should be recalculated to account for the difference in ON resistance and bias voltage limitations between $V_{CC(B)}$ and $V_{CC(A)}$.

Table 6. Pull-up resistor minimum values, 3 mA driver sink current for PCA9306 and NVT20xx

A-side			B-	side		
	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	5.0 V
1.0 V	$R_{pu(A)} = 750 \Omega$	$R_{pu(A)} = 845 \Omega$	$R_{pu(A)} = 976 \Omega$	$R_{pu(A)}$ = none	$R_{pu(A)}$ = none	R _{pu(A)} = none
	$R_{pu(B)} = 750 \Omega$	$R_{pu(B)}$ = 845 Ω	$R_{pu(B)}$ = 976 Ω	$R_{pu(B)}$ = 887 Ω	$R_{pu(B)} = 1.18 \text{ k}\Omega$	$R_{pu(B)}$ = 1.82 k Ω
1.2 V		$R_{pu(A)} = 931 \Omega$	$R_{pu(A)} = 1.02 \text{ k}\Omega$	$R_{pu(A)}$ = none	$R_{pu(A)}$ = none	$R_{pu(A)}$ = none
		$R_{pu(B)}$ = 931 Ω	$R_{pu(B)} = 1.02 \text{ k}\Omega$	$R_{pu(B)}$ = 887 Ω	$R_{pu(B)} = 1.18 \text{ k}\Omega$	$R_{pu(B)}$ = 1.82 k Ω
1.5 V			$R_{pu(A)} = 1.1 \text{ k}\Omega$	$R_{pu(A)}$ = none	$R_{pu(A)}$ = none	R _{pu(A)} = none
			$R_{pu(B)} = 1.1 \text{ k}\Omega$	$R_{pu(B)}$ = 866 Ω	$R_{pu(B)} = 1.18 \text{ k}\Omega$	$R_{pu(B)} = 1.78 \text{ k}\Omega$
1.8 V				$R_{pu(A)} = 1.47 \text{ k}\Omega$	$R_{pu(A)}$ = none	$R_{pu(A)}$ = none
				$R_{pu(B)} = 1.47 \text{ k}\Omega$	$R_{pu(B)} = 1.15 \text{ k}\Omega$	$R_{pu(B)} = 1.78 \text{ k}\Omega$
2.5 V					$R_{pu(A)} = 1.96 \text{ k}\Omega$	$R_{pu(A)}$ = none
					$R_{pu(B)} = 1.96 \text{ k}\Omega$	$R_{pu(B)} = 1.78 \text{ k}\Omega$
3.3 V						R _{pu(A)} = none
						$R_{pu(B)} = 1.74 \text{ k}\Omega$

Table 7. Pull-up resistor minimum values, 10 mA driver sink current for PCA9306 and NVT20xx

A-side			B-	side		
	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	5.0 V
1.0 V	$R_{pu(A)} = 221 \Omega$	$R_{pu(A)} = 255 \Omega$	$R_{pu(A)} = 287 \Omega$	$R_{pu(A)}$ = none	R _{pu(A)} = none	$R_{pu(A)}$ = none
	$R_{pu(B)}$ = 221 Ω	$R_{pu(B)}$ = 255 Ω	$R_{pu(B)}$ = 287 Ω	$R_{pu(B)}$ = 267 Ω	$R_{pu(B)}$ = 357 Ω	$R_{pu(B)} = 549 \Omega$
1.2 V		$R_{pu(A)} = 274 \Omega$	$R_{pu(A)} = 309 \Omega$	$R_{pu(A)}$ = none	$R_{pu(A)}$ = none	$R_{pu(A)}$ = none
		$R_{pu(B)} = 274 \Omega$	$R_{pu(B)} = 309 \Omega$	$R_{pu(B)} = 267 \Omega$	$R_{pu(B)} = 357 \Omega$	$R_{pu(B)} = 549 \Omega$
1.5 V			$R_{pu(A)}$ = 332 Ω	$R_{pu(A)}$ = none	$R_{pu(A)}$ = none	$R_{pu(A)}$ = none
			$R_{pu(B)}$ = 332 Ω	$R_{pu(B)}$ = 261 Ω	$R_{pu(B)} = 348 \Omega$	$R_{pu(B)}$ = 536 Ω
1.8 V				$R_{pu(A)} = 442 \Omega$	$R_{pu(A)}$ = none	$R_{pu(A)}$ = none
				$R_{pu(B)} = 442 \Omega$	$R_{pu(B)}$ = 348 Ω	$R_{pu(B)}$ = 536 Ω
2.5 V					$R_{pu(A)} = 590 \Omega$	$R_{pu(A)}$ = none
					$R_{pu(B)}$ = 590 Ω	$R_{pu(B)}$ = 523 Ω
3.3 V						$R_{pu(A)}$ = none
						$R_{pu(B)}$ = 523 Ω

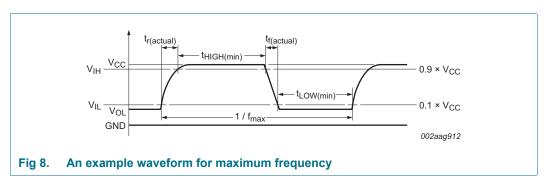
A-side			B-	side		
	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	5.0 V
1.0 V	$R_{pu(A)} = 147 \Omega$	$R_{pu(A)} = 169 \Omega$	$R_{pu(A)} = 191 \Omega$	$R_{pu(A)}$ = none	R _{pu(A)} = none	$R_{pu(A)}$ = none
	$R_{pu(B)} = 147 \Omega$	$R_{pu(B)}$ = 169 Ω	$R_{pu(B)}$ = 191 Ω	$R_{pu(B)}$ = 178 Ω	$R_{pu(B)}$ = 237 Ω	$R_{pu(B)}$ = 365 Ω
1.2 V		$R_{pu(A)}$ = 182 Ω	$R_{pu(A)} = 205 \Omega$	$R_{pu(A)}$ = none	$R_{pu(A)}$ = none	$R_{pu(A)}$ = none
		$R_{pu(B)}$ = 182 Ω	$R_{pu(B)} = 205 \Omega$	$R_{pu(B)} = 178 \Omega$	$R_{pu(B)} = 237 \Omega$	$R_{pu(B)} = 365 \Omega$
1.5 V			$R_{pu(A)} = 221 \Omega$	$R_{pu(A)}$ = none	$R_{pu(A)}$ = none	$R_{pu(A)}$ = none
			$R_{pu(B)} = 221 \Omega$	$R_{pu(B)} = 174 \Omega$	$R_{pu(B)} = 232 \Omega$	$R_{pu(B)} = 357 \Omega$
1.8 V				$R_{pu(A)}$ = 294 Ω	$R_{pu(A)}$ = none	$R_{pu(A)}$ = none
				$R_{pu(B)}$ = 294 Ω	$R_{pu(B)}$ = 232 Ω	$R_{pu(B)} = 357 \Omega$
2.5 V					$R_{pu(A)} = 392 \Omega$	R _{pu(A)} = none
					$R_{pu(B)}$ = 392 Ω	$R_{pu(B)} = 357 \Omega$
3.3 V						R _{pu(A)} = none
						$R_{pu(B)} = 348 \Omega$

Table 8. Pull-up resistor minimum values, 15 mA driver sink current for PCA9306 and NVT20xx

7.4 How to design for maximum frequency operation

The maximum frequency is limited by the minimum pulse width LOW and HIGH as well as rise time and fall time. See Equation 1 as an example of the maximum frequency. The rise and fall times are shown in Figure 8.

$$f_{max} = \frac{1}{t_{LOW(min)} + t_{HIGH(min)} + t_{r(actual)} + t_{f(actual)}}$$
(1)



The rise and fall times are dependent upon translation voltages, the drive strength, the total node capacitance ($C_{L(tot)}$) and the pull-up resistors (R_{PU}) that are present on the bus. The node capacitance is the addition of the PCB trace capacitance and the device capacitance that exists on the bus. Because of the dependency of the external components, PCB layout and the different device operating states the calculation of rise and fall times is complex and has several inflection points along the curve.

The main component of the rise and fall times is the RC time constant of the bus line when the device is in its two primary operating states: when device is in the ON state and it is low-impedance, the other is when the device is OFF isolating the A-side from the B-side.

A description of the fall time applied to either An or Bn output going from HIGH to LOW is as follows. Whichever side is asserted first, the B-side down must discharge to the $V_{CC(A)}$ voltage. The time is determined by the pull-up resistor, pull-down driver strength and the

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capacitance. As the level moves below the $V_{CC(A)}$ voltage, the channel resistance drops so that both A and B sides equal. The capacitance on both sides is connected to form the total capacitance and the pull-up resistors on both sides combine to the parallel equivalent resistance. The R_{on} of the device is small compared to the pull-up resistor values, so its effect on the pull-up resistance can be neglected and the fall is determined by the driver pulling the combined capacitance and pull-up resistor currents. An estimation of the actual fall time seen by the device is equal to the time it takes for the B-side to fall to the $V_{CC(A)}$ voltage and the time it takes for both sides to fall from the $V_{CC(A)}$ voltage to the V_{IL} level.

A description of the rise time applied to either An or Bn output going from LOW to HIGH is as follows. When the signal level is LOW, the R_{on} is at its minimum, so the A and B sides are essentially one node. They will rise together with an RC time constant that is the sum of all the capacitance from both sides and the parallel of the resistance from both sides. As the signal approaches the $V_{CC(A)}$ voltage, the channel resistance goes up and the waveforms separate, with the B side finishing its rise with the RC time constant of the B side. The rise to $V_{CC(A)}$ is essentially the same for both sides.

There are some basic guidelines to follow that will help maximize the performance of the device:

- Keep trace length to a minimum by placing the NVT device close to the processor.
- The signal round trip time on trace should be shorter than the rise or fall time of signal to reduce reflections.
- The faster the edge of the signal, the higher the chance for ringing.
- The higher drive strength controlled by the pull-up resistor (up to 15 mA), the higher the frequency the device can use.

The system designer must design the pull-up resistor value based on external current drive strength and limit the node capacitance (minimize the wire, stub, connector and trace length) to get the desired operation frequency result.

8. Limiting values

Table 9. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Over operating free-air temperature range.

Symbol	Parameter	Conditions		Min	Max	Unit
V _{ref(A)}	reference voltage (A)			-0.5	+6	V
V _{ref(B)}	reference voltage (B)			-0.5	+6	V
VI	input voltage			-0.5 <mark>[1]</mark>	+6	V
V _{I/O}	voltage on an input/output pin			-0.5 <mark>[1]</mark>	+6	V
I _{ch}	channel current (DC)			-	128	mA
I _{IK}	input clamping current	V _I < 0 V		-50	-	mA
I _{OK}	output clamping current		[2]	-50	+50	mA
T _{stg}	storage temperature			-65	+150	°C

^[1] The input and input/output negative voltage ratings may be exceeded if the input and input/output clamp current ratings are observed.

[2] Low duty cycle pulses, not DC because of heating.

9. Recommended operating conditions

Table 10. Operating conditions

Symbol	Parameter	Conditions		Min	Max	Unit
V _{I/O}	voltage on an input/output pin	An, Bn		0	5.5	V
V _{ref(A)}	reference voltage (A)	VREFA	[1]	0	5.4	V
V _{ref(B)}	reference voltage (B)	VREFB	[1]	0	5.5	V
$V_{I(EN)}$	input voltage on pin EN			0	5.5	V
I _{sw(pass)}	pass switch current			-	64	mA
T _{amb}	ambient temperature	operating in free-air		-40	+105	°C

^[1] $V_{ref(A)} \le V_{ref(B)} - 1 \text{ V}$ for best results in level shifting applications.

10. Static characteristics

Table 11. Static characteristics

 T_{amb} = -40 °C to +105 °C, unless otherwise specified.

Symbol	Parameter	Conditions		Min	Typ[1]	Max	Unit
V _{IK}	input clamping voltage	$I_I = -18 \text{ mA}; V_{I(EN)} = 0 \text{ V}$		-	-	-1.2	V
I _{IH}	HIGH-level input current	$V_{I} = 5 \text{ V}; V_{I(EN)} = 0 \text{ V}$		-	-	5	μА
C _{i(EN)}	input capacitance on pin EN	V _I = 3 V or 0 V		-	7.1	-	pF
$C_{io(off)}$	off-state input/output capacitance	An, Bn; V _O = 3 V or 0 V; V _{I(EN)} = 0 V		-	4	6	pF
C _{io(on)}	on-state input/output capacitance	An, Bn; V _O = 3 V or 0 V; V _{I(EN)} = 3 V		-	9.3	12.5[2]	pF
R _{on}	ON-state resistance	An, Bn; V _I = 0 V; I _O = 64 mA; V _{I(EN)} = 4.5 V	[3][4][5]	1	2.4	5.0	Ω
		V _I = 2.4 V; I _O = 15 mA; V _{I(EN)} = 4.5 V	[3][4]	-	4.8	7.5	Ω

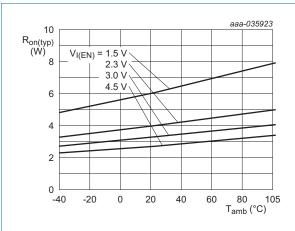
^[1] All typical values are at $T_{amb} = 25 \,^{\circ}C$.

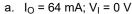
^[2] Not production tested, maximum value based on characterization data of typical parts.

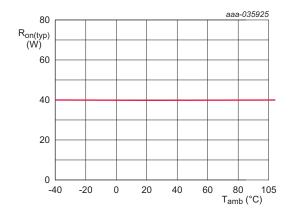
^[3] Measured by the voltage drop between the An and Bn terminals at the indicated current through the switch. ON-state resistance is determined by the lowest voltage of the two terminals.

^[4] See curves in Figure 9 for typical temperature and $V_{I(EN)}$ behavior.

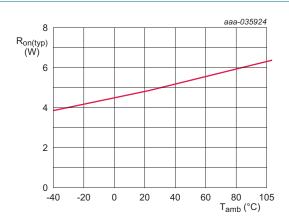
^[5] Guaranteed by design.



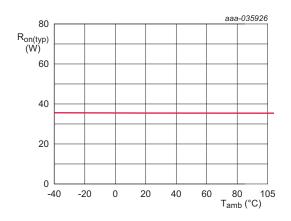




c. $I_O = 15 \text{ mA}$; $V_I = 2.4 \text{ V}$; $V_{I(EN)} = 3.0 \text{ V}$



b. $I_O = 15 \text{ mA}$; $V_I = 2.4 \text{ V}$; $V_{I(EN)} = 4.5 \text{ V}$



d. $I_O = 15 \text{ mA}$; $V_I = 1.7 \text{ V}$; $V_{I(EN)} = 2.3 \text{ V}$

Typical ON-state resistance versus ambient temperature

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11. Dynamic characteristics

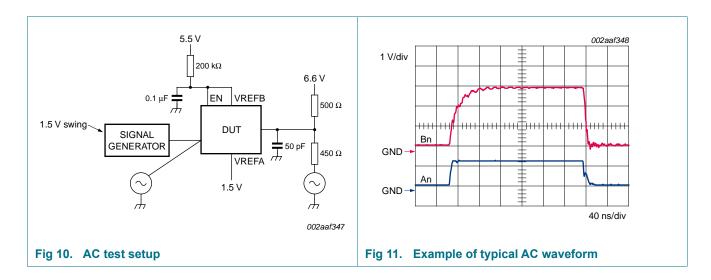
11.1 Open-drain drivers

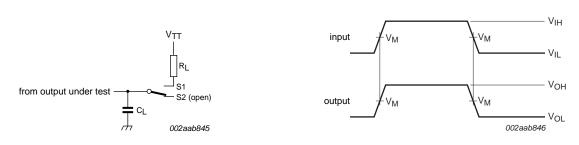
Table 12. Dynamic characteristics for open-drain drivers

 T_{amb} = -40 °C to +105 °C; $V_{I(EN)}$ = $V_{ref(B)}$; $R_{bias(ext)}$ = 200 k Ω ; C_{VREFB} = 0.1 μ F; unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Refer to	igure 12						
t _{PLH}	LOW to HIGH propagation delay	from (input) Bn to (output) An	[1]	R _{on} ×	(C _L + C	io(on)	ns
t _{PHL}	HIGH to LOW propagation delay	from (input) Bn to (output) An		R _{on} ×	(C _L + C	io(on)	ns

[1] See graphs based on R_{on} typical and $C_{io(on)}$ + C_L = 50 pF.





a. Load circuit

b. Timing diagram; high-impedance scope probe used

S2 = translating down, and same voltage.

 C_L includes probe and jig capacitance.

All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz; Z_o = 50 Ω ; $t_r \leq$ 2 ns; $t_f \leq$ 2 ns. The outputs are measured one at a time, with one transition per measurement.

Fig 12. Load circuit for outputs

NVT2001 NVT2002

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12. Performance curves

 t_{PLH} up-translation is typically dominated by the RC time constant, i.e., $C_{L(tot)} \times R_{PU}$ = 50 pF \times 197 Ω = 9.85 ns, but the $R_{on} \times C_{L(tot)}$ = 50 pF \times 5 Ω = 0.250 ns.

 t_{PHL} is typically dominated by the external pull-down driver + R_{on} , which is typically small compared to the t_{PLH} in an up-translation case.

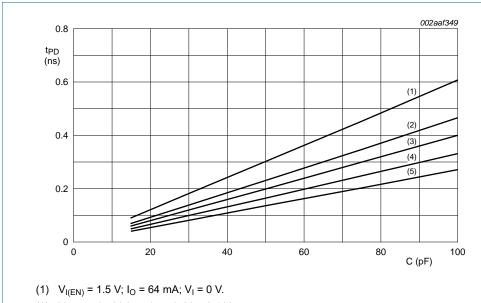
Enable/disable times are dominated by the RC time constant on the EN pin since the transistor turn off is on the order of ns, but the enable RC is on the order of ms.

Fall time is dominated by the external pull-down driver with only a slight R_{on} addition.

Rise time is dominated by the $R_{PU} \times C_L$.

Skew time within the part is virtually non-existent, dominated by the difference in bond wire lengths, which is typically small compared to the board-level routing differences.

Maximum data rate is dominated by the system capacitance and pull-up resistors.



- (2) $V_{I(EN)} = 4.5 \text{ V}$; $I_O = 15 \text{ mA}$; $V_I = 2.4 \text{ V}$.
- (3) $V_{I(EN)} = 2.3 \text{ V}$; $I_O = 64 \text{ mA}$; $V_I = 0 \text{ V}$.
- (4) $V_{I(EN)} = 3.0 \text{ V}$; $I_O = 64 \text{ mA}$; $V_I = 0 \text{ V}$.
- (5) $V_{I(EN)} = 4.5 \text{ V}$; $I_O = 64 \text{ mA}$; $V_I = 0 \text{ V}$.

Fig 13. Typical capacitance versus propagation delay

13. Package outline

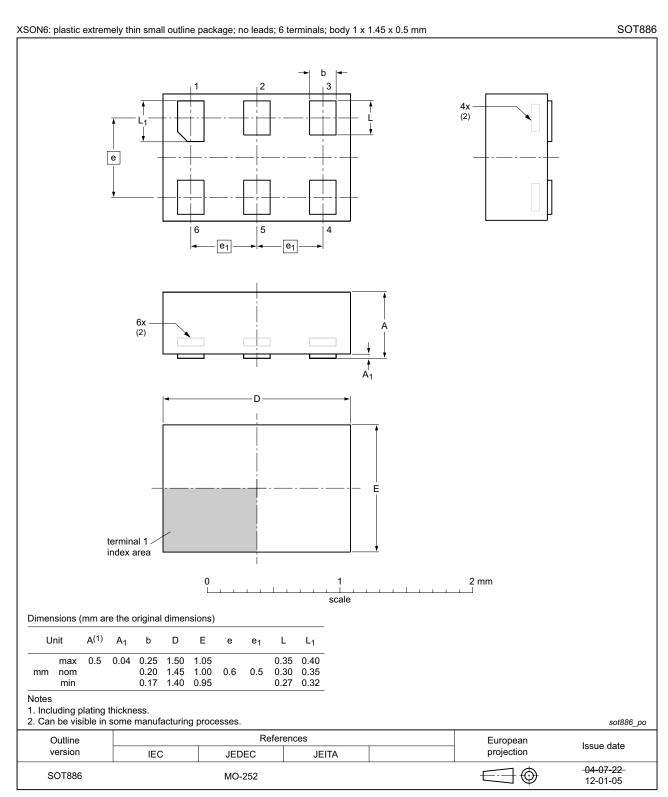


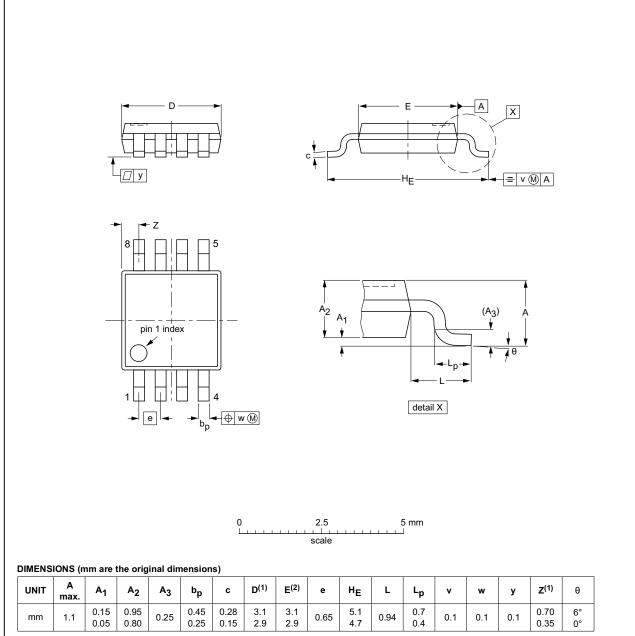
Fig 14. Package outline SOT886 (XSON6)

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TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm

SOT505-1



Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE	REFERENCES				EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA		PROJECTION	1330E DATE
SOT505-1						99-04-09 03-02-18

Fig 15. Package outline SOT505-1 (TSSOP8)

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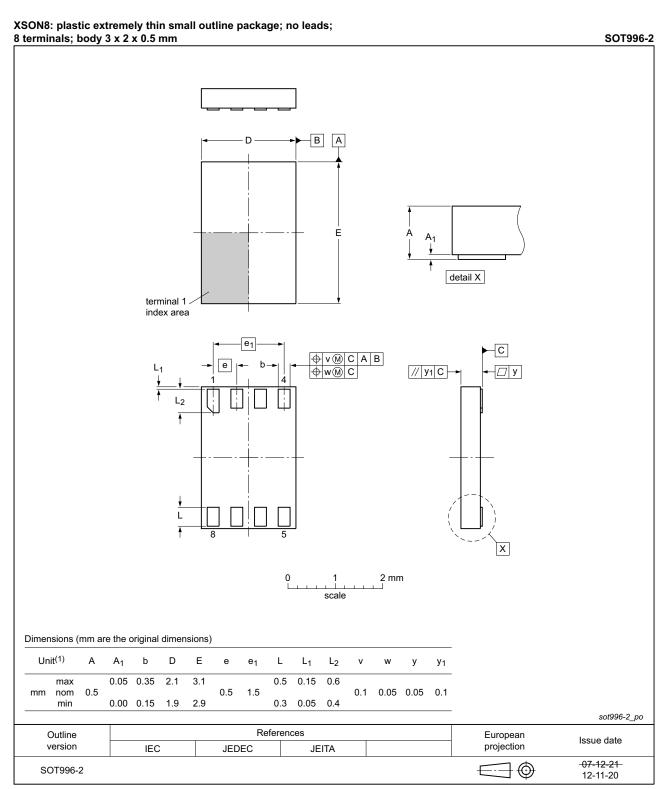


Fig 16. Package outline SOT996-2 (XSON8U)

14. Soldering of SMD packages

This text provides a very brief insight into a complex technology. A more in-depth account of soldering ICs can be found in Application Note *AN10365 "Surface mount reflow soldering description"*.

14.1 Introduction to soldering

Soldering is one of the most common methods through which packages are attached to Printed Circuit Boards (PCBs), to form electrical circuits. The soldered joint provides both the mechanical and the electrical connection. There is no single soldering method that is ideal for all IC packages. Wave soldering is often preferred when through-hole and Surface Mount Devices (SMDs) are mixed on one printed wiring board; however, it is not suitable for fine pitch SMDs. Reflow soldering is ideal for the small pitches and high densities that come with increased miniaturization.

14.2 Wave and reflow soldering

Wave soldering is a joining technology in which the joints are made by solder coming from a standing wave of liquid solder. The wave soldering process is suitable for the following:

- Through-hole components
- Leaded or leadless SMDs, which are glued to the surface of the printed circuit board

Not all SMDs can be wave soldered. Packages with solder balls, and some leadless packages which have solder lands underneath the body, cannot be wave soldered. Also, leaded SMDs with leads having a pitch smaller than ~0.6 mm cannot be wave soldered, due to an increased probability of bridging.

The reflow soldering process involves applying solder paste to a board, followed by component placement and exposure to a temperature profile. Leaded packages, packages with solder balls, and leadless packages are all reflow solderable.

Key characteristics in both wave and reflow soldering are:

- · Board specifications, including the board finish, solder masks and vias
- Package footprints, including solder thieves and orientation
- The moisture sensitivity level of the packages
- Package placement
- · Inspection and repair
- Lead-free soldering versus SnPb soldering

14.3 Wave soldering

Key characteristics in wave soldering are:

- Process issues, such as application of adhesive and flux, clinching of leads, board transport, the solder wave parameters, and the time during which components are exposed to the wave
- · Solder bath specifications, including temperature and impurities

14.4 Reflow soldering

Key characteristics in reflow soldering are:

- Lead-free versus SnPb soldering; note that a lead-free reflow process usually leads to higher minimum peak temperatures (see <u>Figure 17</u>) than a SnPb process, thus reducing the process window
- Solder paste printing issues including smearing, release, and adjusting the process window for a mix of large and small components on one board
- Reflow temperature profile; this profile includes preheat, reflow (in which the board is heated to the peak temperature) and cooling down. It is imperative that the peak temperature is high enough for the solder to make reliable solder joints (a solder paste characteristic). In addition, the peak temperature must be low enough that the packages and/or boards are not damaged. The peak temperature of the package depends on package thickness and volume and is classified in accordance with Table 13 and 14

Table 13. SnPb eutectic process (from J-STD-020D)

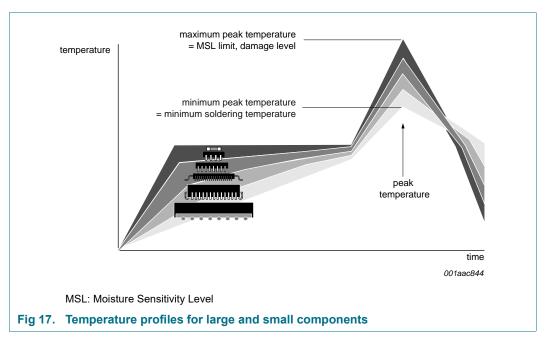
Package thickness (mm)	Package reflow temperature (°C) Volume (mm³)		
	< 350	≥ 350	
< 2.5	235	220	
≥ 2.5	220	220	

Table 14. Lead-free process (from J-STD-020D)

Package thickness (mm)	Package reflow temperature (°C)			
	Volume (mm³)			
	< 350	350 to 2000	> 2000	
< 1.6	260	260	260	
1.6 to 2.5	260	250	245	
> 2.5	250	245	245	

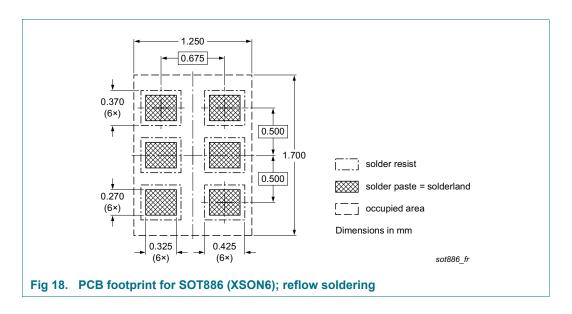
Moisture sensitivity precautions, as indicated on the packing, must be respected at all times.

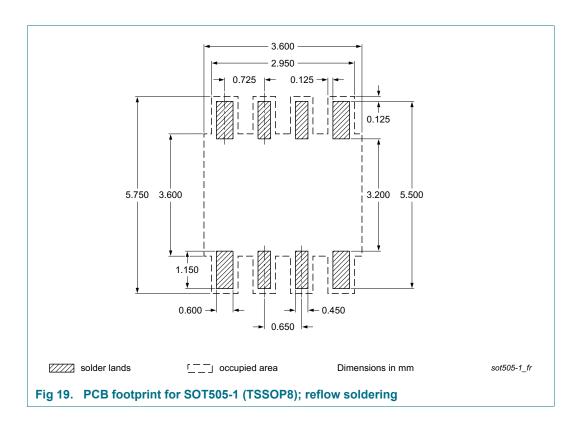
Studies have shown that small packages reach higher temperatures during reflow soldering, see Figure 17.



For further information on temperature profiles, refer to Application Note *AN10365* "Surface mount reflow soldering description".

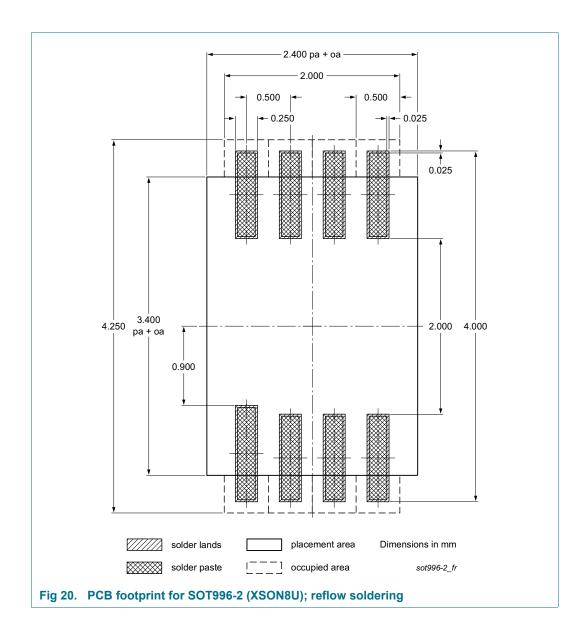
15. Soldering: PCB footprints





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16. Abbreviations

Table 15. Abbreviations

Acronym	Description
CDM	Charged Device Model
ESD	ElectroStatic Discharge
GTL	Gunning Transceiver Logic
НВМ	Human Body Model
I ² C-bus	Inter-Integrated Circuit bus
I/O	Input/Output
LVTTL	Low Voltage Transistor-Transistor Logic
PRR	Pulse Repetition Rate
RC	Resistor-Capacitor network

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17. Revision history

Table 16. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
NVT2001_NVT2002 v.4.1	20191206	Product data sheet	201909001A, 201912004I	NVT2001_NVT2002 v.4	
Modifications:	 Package SOT886 requiring SSB added. Refer to PCN number 201909001A XSON6 (SOT886) Assembly/Test Transfer from ATGD and ATSN to ATBK. 				
	 Corrected NVT2001GM topside mark N1X to N1. Only two characters allowed in Line 1 and there is no revolving date code. 				
	 Improved ten 	nperature range from "-40 °C to	+85 °C" to "-40 °C	to +105 °C"	
NVT2001_NVT2002 v.4	20140127	Product data sheet	-	NVT2001_NVT2002 v.3	
Modifications:	Added Section 3.1 "Ordering options"				
	Deleted (old)	d) Section 7.3 "Sizing pull-up resistor"			
	Added (new) Section 7.3 "How to size pull-up resistor value"				
	Added (new) Section 7.4 "How to design for maximum frequency operation"				
	Added (new)	Section 15 "Soldering: PCB fo	otprints"		
NVT2001_NVT2002 v.3	20120426	Product data sheet	-	NVT2001_NVT2002 v.2	
NVT2001_NVT2002 v.2	20111026	Product data sheet	-	NVT2001_NVT2002 v.1	
NVT2001_NVT2002 v.1	20100830	Product data sheet	-	-	

18. Legal information

18.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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